

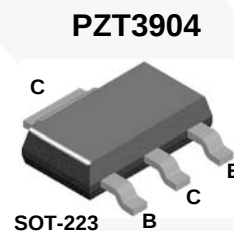
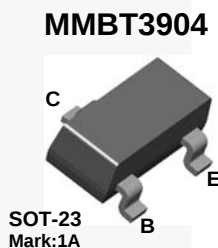
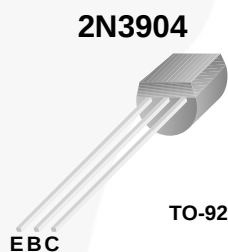


October 2014

2N3904 / MMBT3904 / PZT3904 NPN General-Purpose Amplifier

Description

This device is designed as a general-purpose amplifier and switch. The useful dynamic range extends to 100 mA as a switch and to 100 MHz as an amplifier.



Ordering Information

Part Number	Marking	Package	Packing Method	Pack Quantity
2N3904BU	2N3904	TO-92 3L	Bulk	10000
2N3904TA	2N3904	TO-92 3L	Ammo	2000
2N3904TAR	2N3904	TO-92 3L	Ammo	2000
2N3904TF	2N3904	TO-92 3L	Tape and Reel	2000
2N3904TFR	2N3904	TO-92 3L	Tape and Reel	2000
MMBT3904	1A	SOT-23 3L	Tape and Reel	3000
PZT3904	3904	SOT-223 4L	Tape and Reel	2500

2N3904 / MMBT3904 / PZT3904 — NPN General-Purpose Amplifier

Absolute Maximum Ratings^{(1), (2)}

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Emitter Voltage	40	V
V_{CBO}	Collector-Base Voltage	60	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector Current - Continuous	200	mA
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Notes:

- These ratings are based on a maximum junction temperature of 150°C .
- These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty cycle operations.

Thermal Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Maximum			Unit
		2N3904	MMBT3904 ⁽³⁾	PZT3904 ⁽⁴⁾	
P_D	Total Device Dissipation	625	350	1,000	mW
	Derate Above 25°C	5.0	2.8	8.0	mW/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	$^\circ\text{C/W}$

Notes:

- Device is mounted on FR-4 PCB 1.6 inch X 1.6 inch X 0.06 inch.
- Device is mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm, mounting pad for the collector lead minimum 6 cm^2 .

Electrical Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
OFF CHARACTERISTICS					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 1.0 mA, I _B = 0	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 10 μA, I _E = 0	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 10 μA, I _C = 0	6.0		V
I _{BL}	Base Cut-Off Current	V _{CE} = 30 V, V _{EB} = 3 V		50	nA
I _{CEX}	Collector Cut-Off Current	V _{CE} = 30 V, V _{EB} = 3 V		50	nA
ON CHARACTERISTICS ⁽⁵⁾					
h _{FE}	DC Current Gain	I _C = 0.1 mA, V _{CE} = 1.0 V	40		
		I _C = 1.0 mA, V _{CE} = 1.0 V	70		
		I _C = 10 mA, V _{CE} = 1.0 V	100	300	
		I _C = 50 mA, V _{CE} = 1.0 V	60		
		I _C =100 mA, V _{CE} = 1.0V	30		
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 10 mA, I _B = 1.0 mA		0.2	V
		I _C = 50 mA, I _B = 5.0 mA		0.3	
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 10 mA, I _B = 1.0 mA	0.65	0.85	V
		I _C = 50 mA, I _B = 5.0 mA		0.95	
SMALL SIGNAL CHARACTERISTICS					
f _T	Current Gain - Bandwidth Product	I _C = 10 mA, V _{CE} = 20 V, f = 100 MHz	300		MHz
C _{obo}	Output Capacitance	V _{CB} = 5.0 V, I _E = 0, f = 100 kHz		4.0	pF
C _{ibo}	Input Capacitance	V _{EB} = 0.5 V, I _C = 0, f = 100 kHz		8.0	pF
NF	Noise Figure	I _C = 100 μA, V _{CE} = 5.0 V, R _S = 1.0 kΩ, f = 10 Hz to 15.7 kHz		5.0	dB
SWITCHING CHARACTERISTICS					
t _d	Delay Time	V _{CC} = 3.0 V, V _{BE} = 0.5 V		35	ns
t _r	Rise Time	I _C = 10 mA, I _{B1} = 1.0 mA		35	ns
t _s	Storage Time	V _{CC} = 3.0 V, I _C = 10 mA,		200	ns
t _f	Fall Time	I _{B1} = I _{B2} = 1.0 mA		50	ns

Note:

5. Pulse test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2.0\%$.

Typical Performance Characteristics

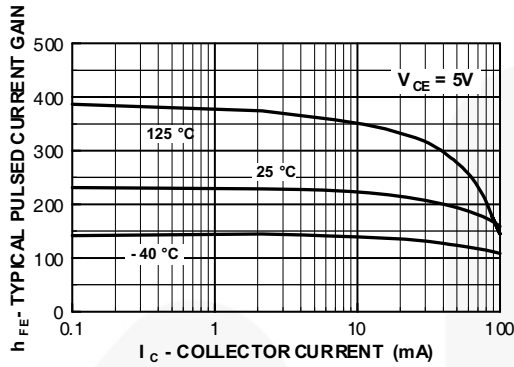


Figure 1. Typical Pulsed Current Gain vs. Collector Current

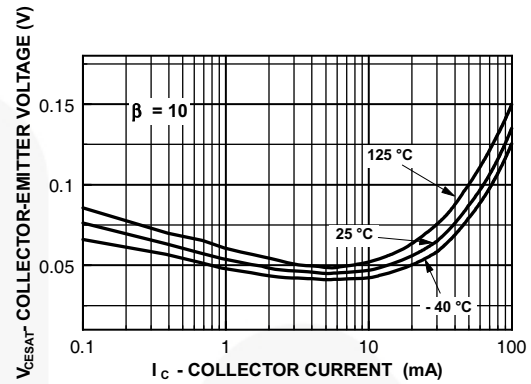


Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

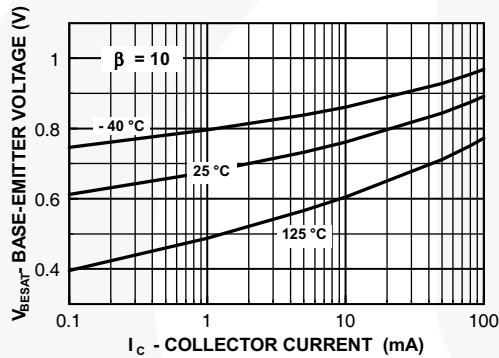


Figure 3. Base-Emitter Saturation Voltage vs. Collector Current

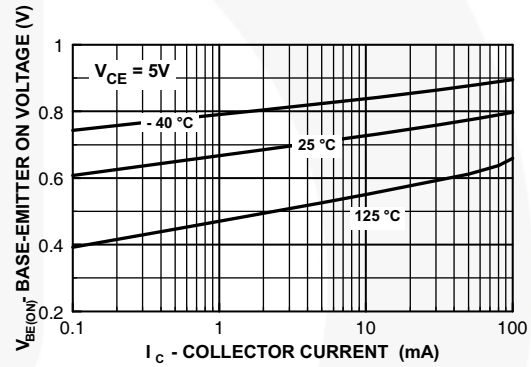


Figure 4. Base-Emitter On Voltage vs. Collector Current

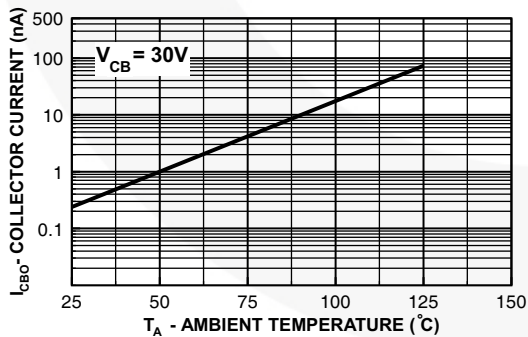


Figure 5. Collector Cut-Off Current vs. Ambient Temperature

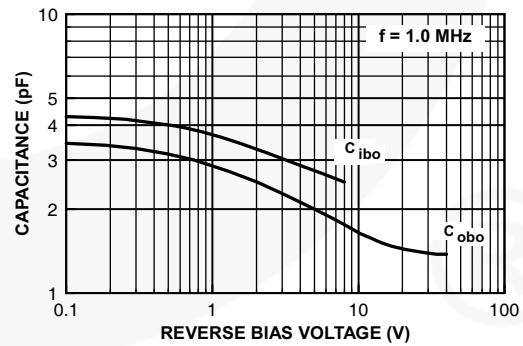


Figure 6. Capacitance vs. Reverse Bias Voltage

Typical Performance Characteristics (Continued)

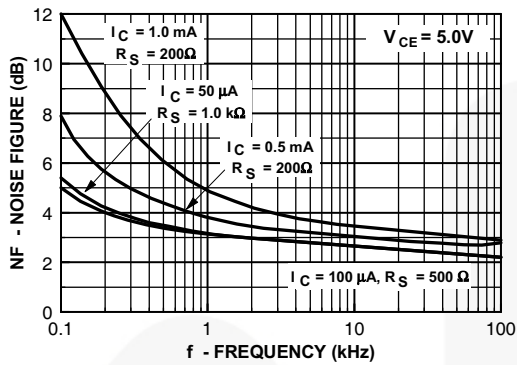


Figure 7. Noise Figure vs. Frequency

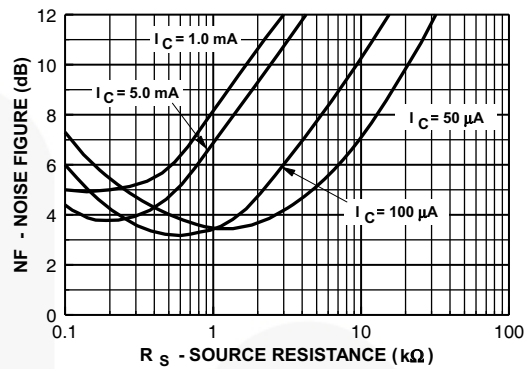


Figure 8. Noise Figure vs. Source Resistance

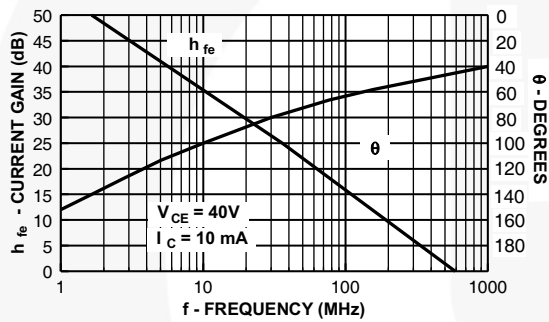


Figure 9. Current Gain and Phase Angle vs. Frequency

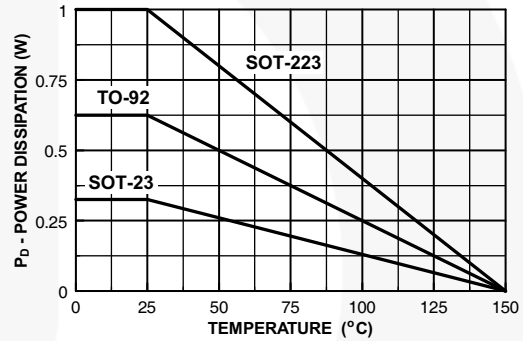


Figure 10. Power Dissipation vs. Ambient Temperature

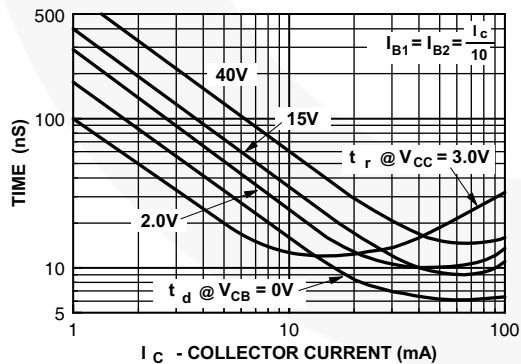


Figure 11. Turn-On Time vs. Collector Current

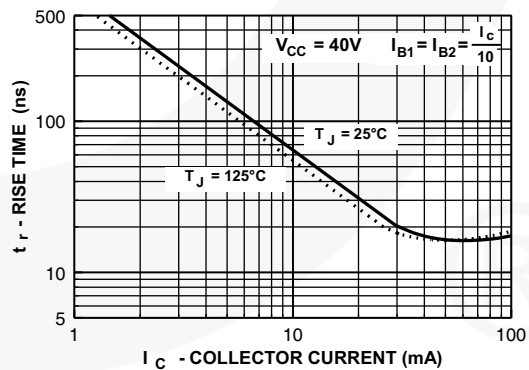


Figure 12. Rise Time vs. Collector Current

Typical Performance Characteristics (Continued)

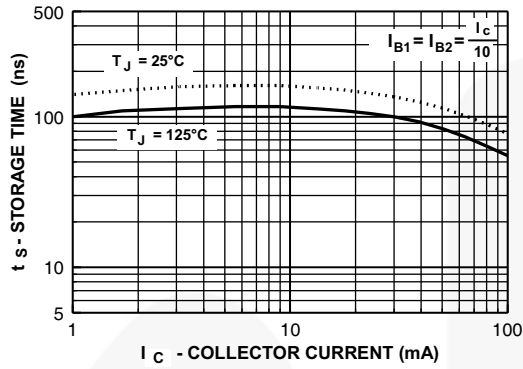


Figure 13. Storage Time vs. Collector Current

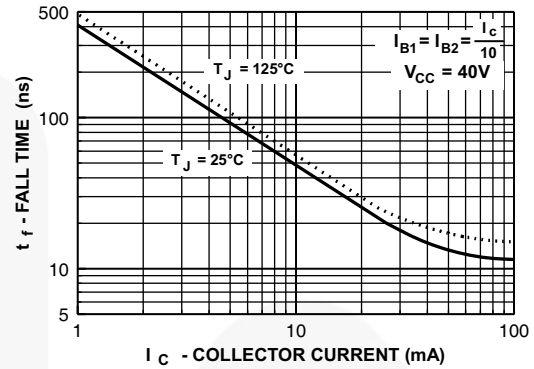


Figure 14. Fall Time vs. Collector Current

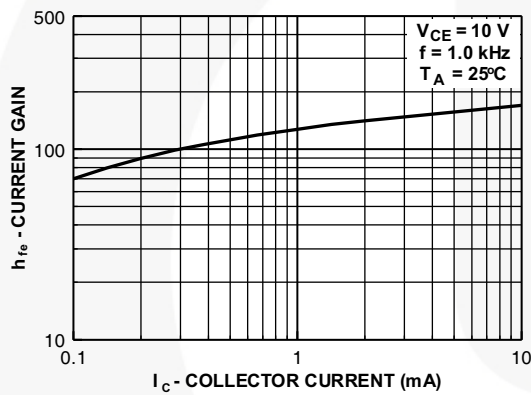


Figure 15. Current Gain

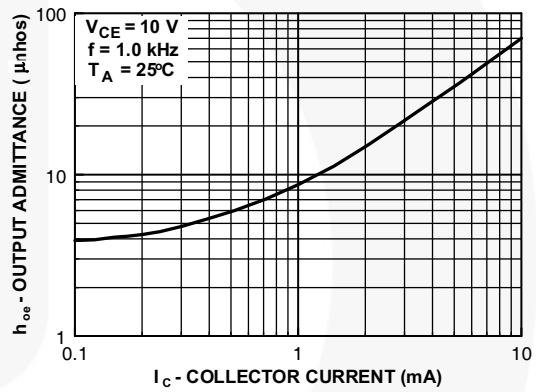


Figure 16. Output Admittance

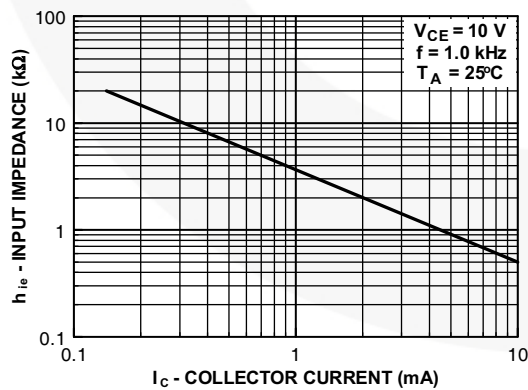


Figure 17. Input Impedance

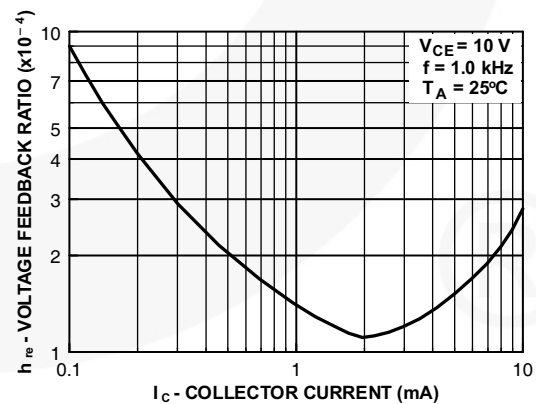


Figure 18. Voltage Feedback Ratio

Test Circuits

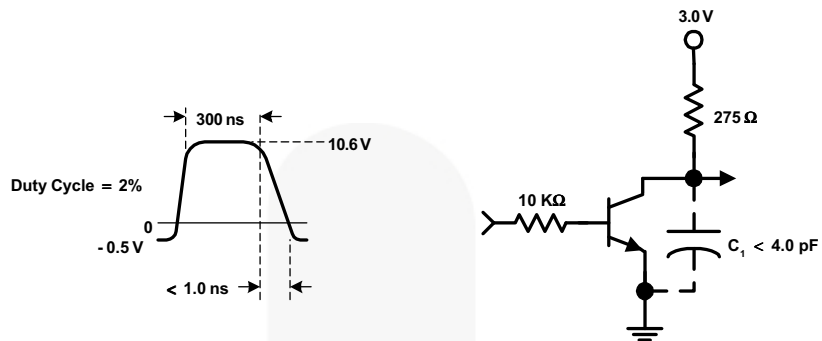


Figure 19. Delay and Rise Time Equivalent Test Circuit

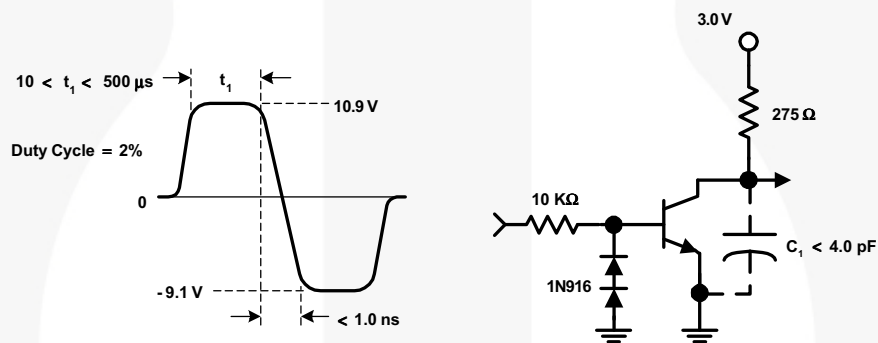
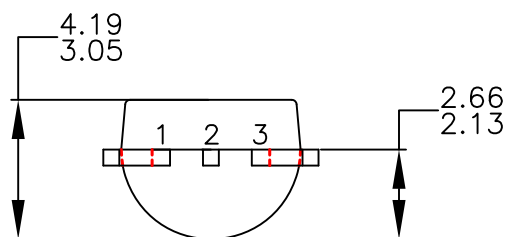
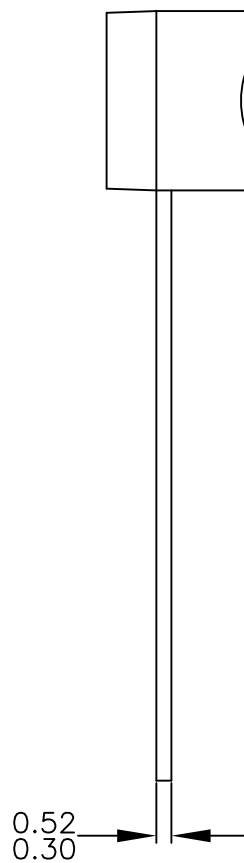
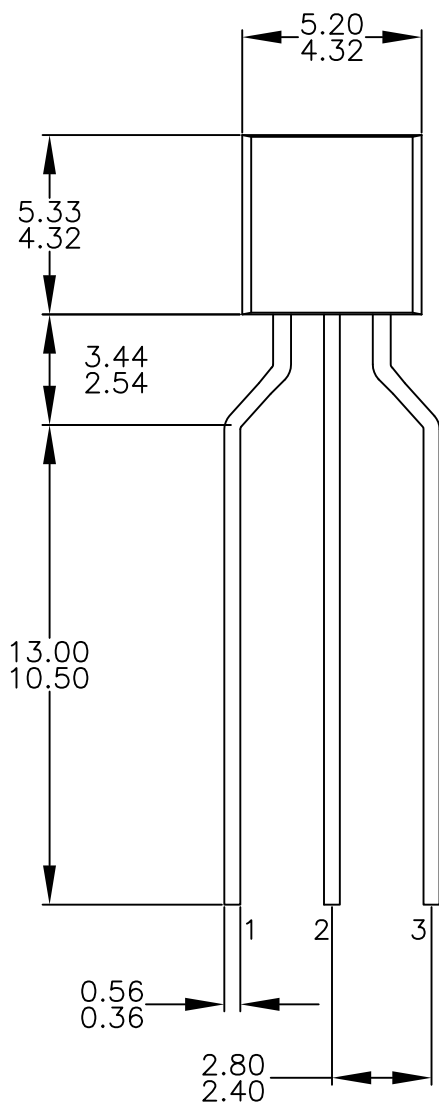
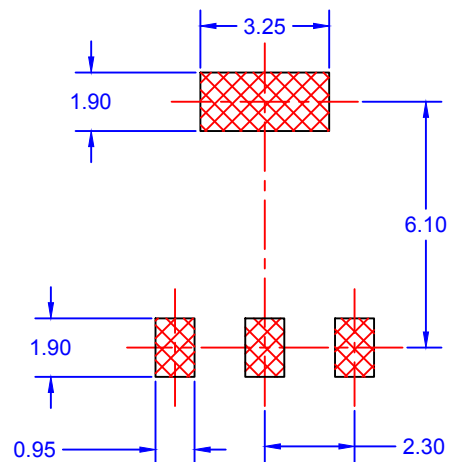


Figure 20. Storage and Fall Time Equivalent Test Circuit

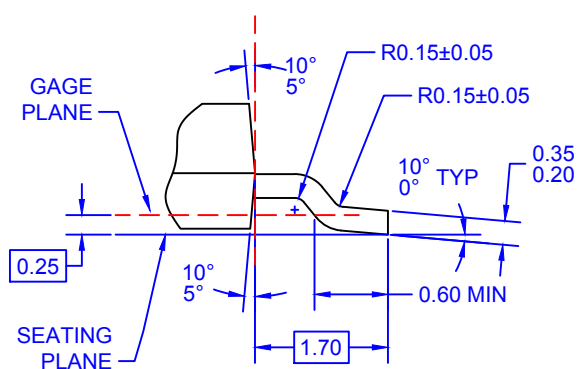
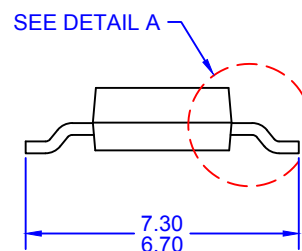
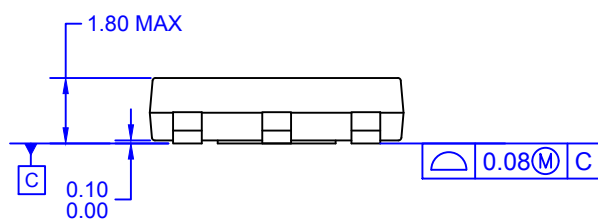


NOTES: UNLESS OTHERWISE SPECIFIED

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- ALL DIMENSIONS ARE IN MILLIMETERS.
- DRAWING CONFORMS TO ASME Y14.5M-2009.
- DRAWING FILENAME: MKT-ZA03FREV3.
- FAIRCHILD SEMICONDUCTOR.



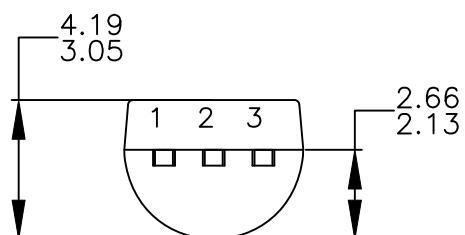
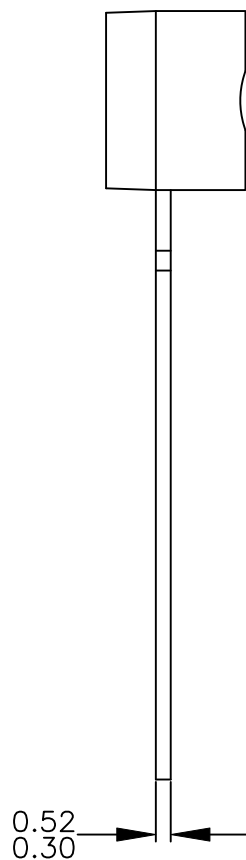
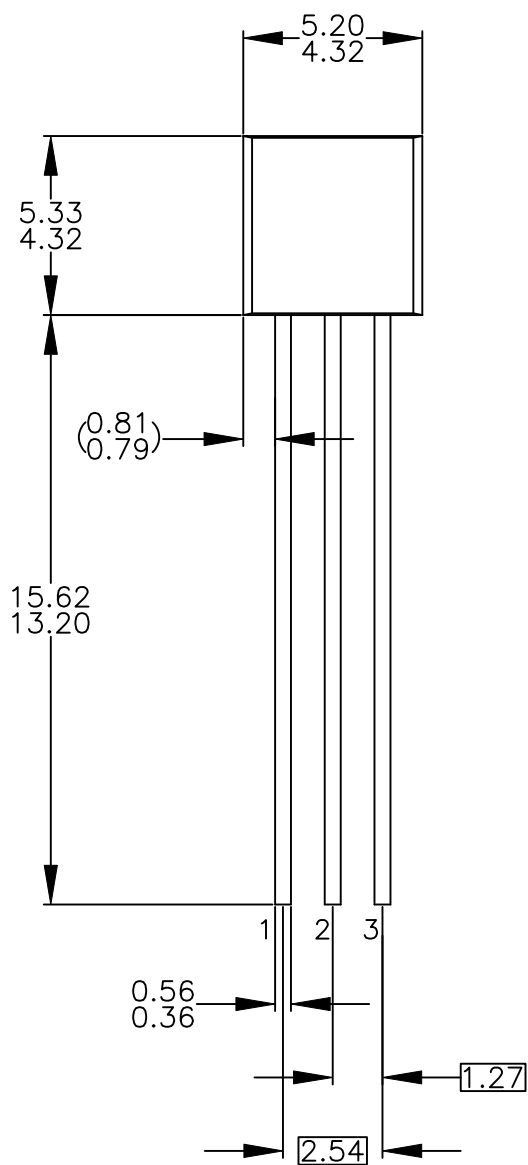
LAND PATTERN RECOMMENDATION



DETAIL A
SCALE: 2:1

- NOTES: UNLESS OTHERWISE SPECIFIED
- A) DRAWING BASED ON JEDEC REGISTRATION TO-261C, VARIATION AA.
 - B) ALL DIMENSIONS ARE IN MILLIMETERS.
 - C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
 - D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
 - E) LANDPATTERN NAME: SOT23P700X180-4BN
 - F) DRAWING FILENAME: MKT-MA04AREV3

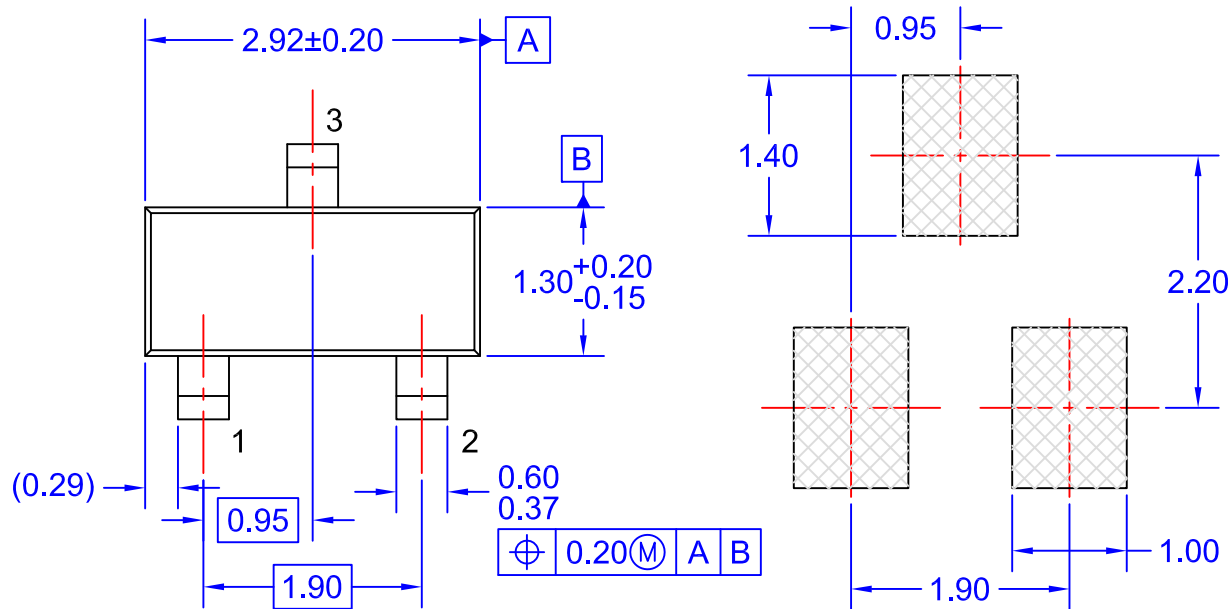




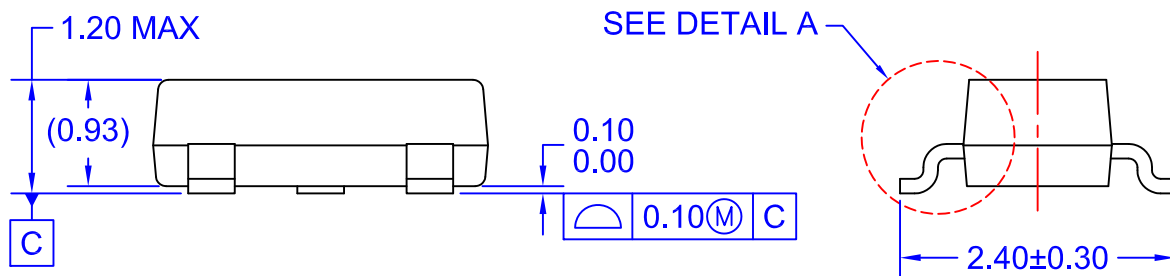
NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-2009.
- D) DRAWING FILENAME: MKT-ZA03DREV4.

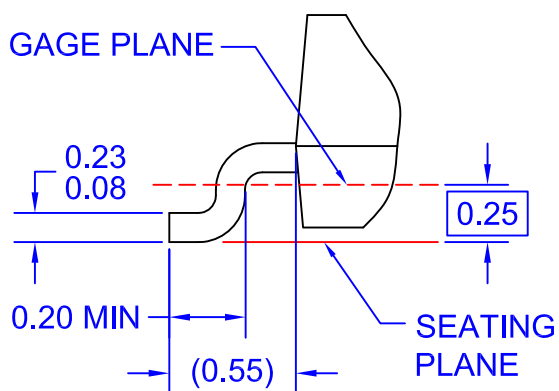




LAND PATTERN
RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED



DETAIL A
SCALE: 2X

- A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 2009.
- E) DRAWING FILE NAME: MA03DREV12



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